

# 50 V, 180 mA P-channel Trench MOSFET Rev. 1 — 23 May 2011

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology

#### 1.3 Applications

- Relay driver
- High-speed line driver

- ESD protection up to 1 kV
- AEC-Q101 qualified
- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

#### Table 1. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage	$T_j = 25 \ ^{\circ}C$	-	-	-50	V
gate-source voltage		-20	-	20	V
drain current	$V_{GS} = -10 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}$ [1]	-	-	-180	mA
racteristics					
drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = -10 \ V; I_D = -100 \ mA; \\ T_j = 25 \ ^\circ C \end{array}$	-	4.5	7.5	Ω
	drain-source voltage gate-source voltage drain current racteristics drain-source on-state	$\begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \textbf{V}_{GS} = -10 \text{ V};  \text{T}_{amb} = 25 ^\circ \text{C} \end{array} \begin{array}{c} \text{[1]} \\ \text{racteristics} \\ \\ \text{drain-source on-state} \\ \end{array} \\ \begin{array}{c} \text{V}_{GS} = -10 \text{ V};  \text{I}_{D} = -100 \text{ mA}; \end{array}$	$\begin{array}{c} \mbox{drain-source voltage} & T_{j} = 25 \ ^{\circ}\ C & - \\ \mbox{gate-source voltage} & & -20 \\ \mbox{drain current} & V_{GS} = -10 \ V; \ T_{amb} = 25 \ ^{\circ}\ C & \ \hline 1 \\ \mbox{racteristics} & & \\ \mbox{drain-source on-state} & V_{GS} = -10 \ V; \ I_{D} = -100 \ mA; & - \end{array}$	$\begin{array}{c} \text{drain-source voltage} \\ \text{drain-source voltage} \\ \text{drain current} \\ \text{drain current} \\ \text{drain-source on-state} \\ \end{array} \begin{array}{c} T_{j} = 25 \ ^{\circ}\text{C} \\ \text{-} \\ \text$	$\begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \text{drain source on-state} \\ \end{array} \begin{array}{c} T_{j} = 25 \ ^{\circ}\text{C} \\ -20 \\ \text{-20} \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ -20 \\ $

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source		
3	D	drain	1 ☐ ☐ 2 SOT23 (TO-236AB)	G Sym146

# 3. Ordering information

Table 3.	Ordering in	formation		
Type numb	ber	Package		
		Name	Description	Version
BSS84AK		TO-236AB	plastic surface-mounted package; 3 leads	SOT23

## 4. Marking

Table 4. Marking codes	
Type number	Marking code <sup>[1]</sup>
BSS84AK	%VS

[1] % = placeholder for manufacturing site code

### 5. Limiting values

#### Table 5. Limiting values

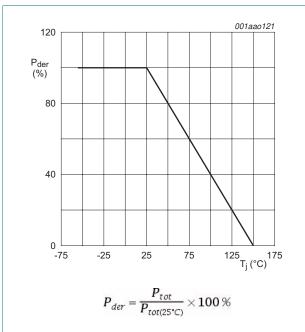
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-50	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = -10 V; $T_{amb}$ = 25 °C	<u>[1]</u>	-	-180	mA
		$V_{GS} = -10 \text{ V}; \text{ T}_{amb} = 100 \text{ °C}$	<u>[1]</u>	-	-120	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-0.7	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	350	mW
			[1]	-	420	mW
		T <sub>sp</sub> = 25 °C		-	1140	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	in diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-180	mA
ESD maxim	um rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	1000	V

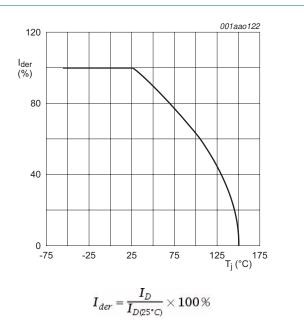
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



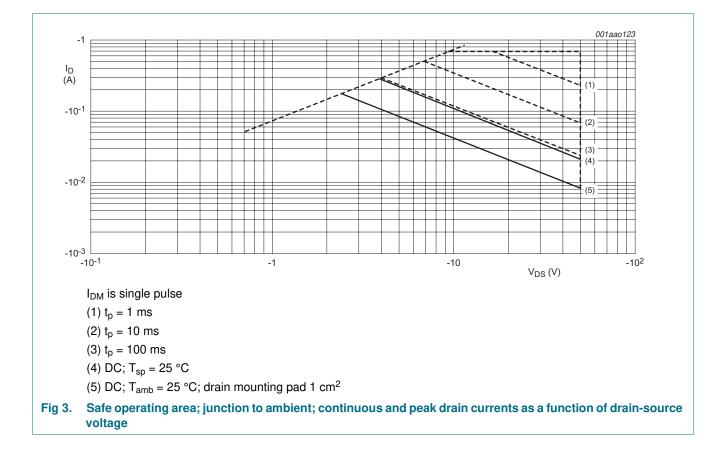






# BSS84AK

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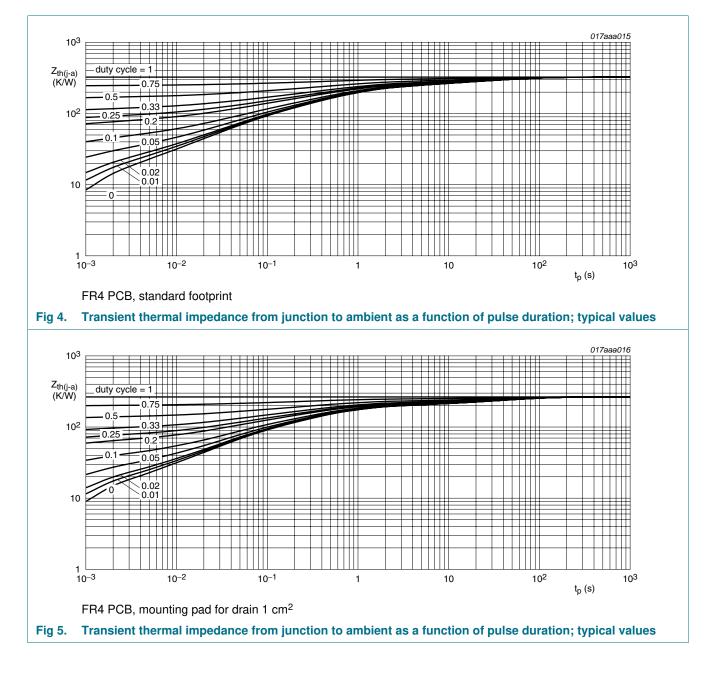


### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	310	370	K/W
			[2] _	260	300	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	115	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

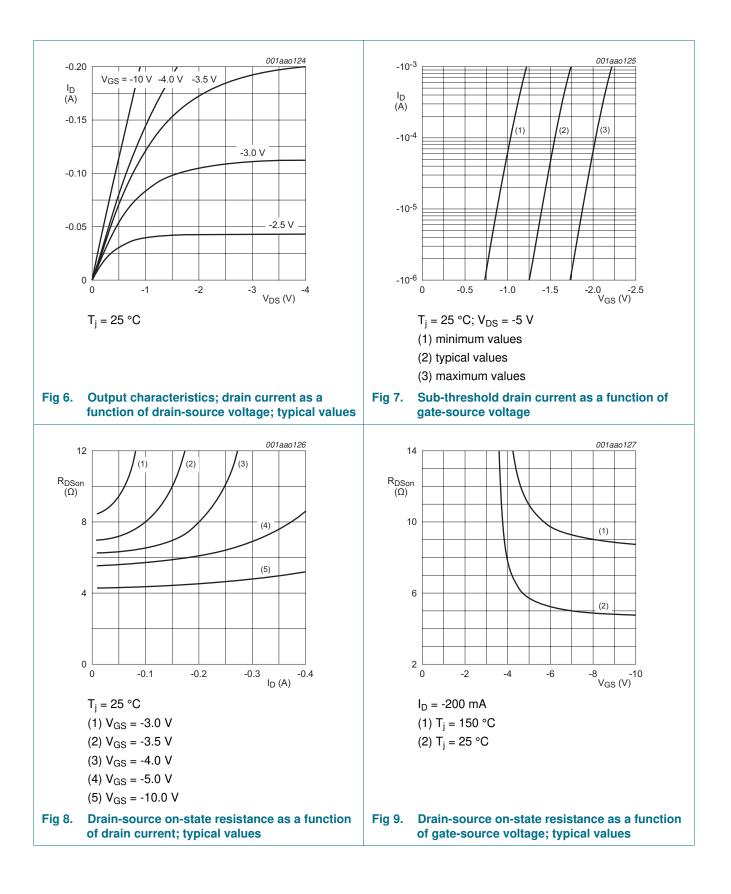


# 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -10 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	-50	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = -250 \ \mu A; V_{DS} = V_{GS}; T_j = 25 \ ^\circ C$	-1.1	-1.6	-2.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-2	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -10 V; I <sub>D</sub> = -100 mA; T <sub>j</sub> = 25 °C	-	4.5	7.5	Ω
	resistance	$V_{GS}$ = -10 V; I <sub>D</sub> = -100 mA; T <sub>j</sub> = 150 °C	-	8	13.5	Ω
		$V_{GS} = -5 \text{ V}; \text{ I}_{D} = -100 \text{ mA}; \text{ T}_{j} = 25 \text{ °C}$	-	5.7	8.5	Ω
<b>g</b> <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -100 mA; $T_j$ = 25 °C	-	150	-	mS
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -25 V; I <sub>D</sub> = -200 mA; V <sub>GS</sub> = -5 V;	-	0.26	0.35	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.09	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = -25 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	24	36	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	4.5	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}=-30~V;~R_L=250~\Omega;~V_{GS}=-10~V;$	-	13	26	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}$	-	11	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	48	96	ns
t <sub>f</sub>	fall time		-	25	-	ns
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -115 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-0.48	-0.85	-1.2	V

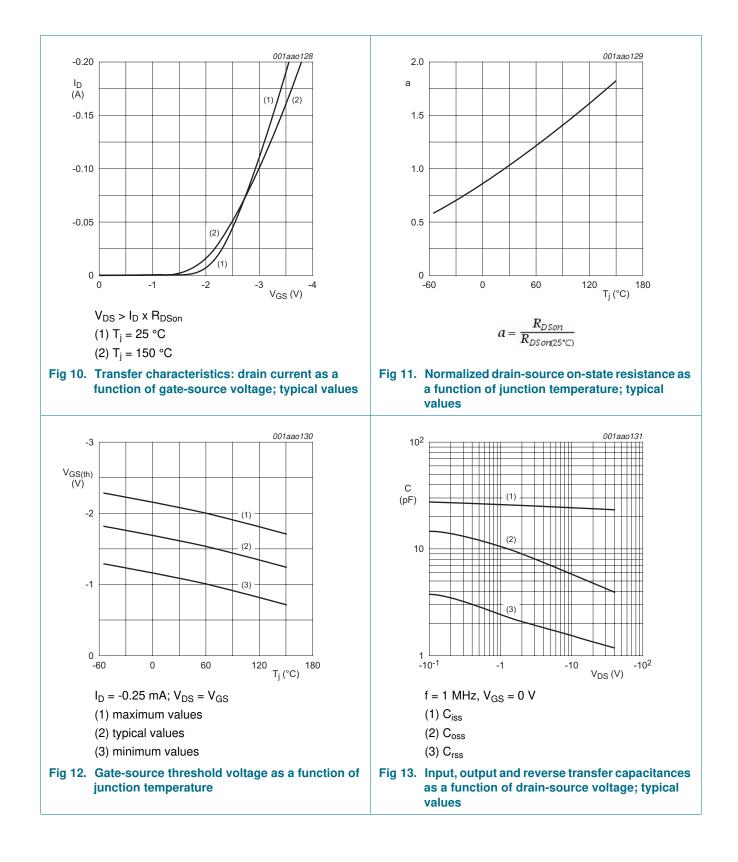
# **BSS84AK**

#### 50 V, 180 mA P-channel Trench MOSFET



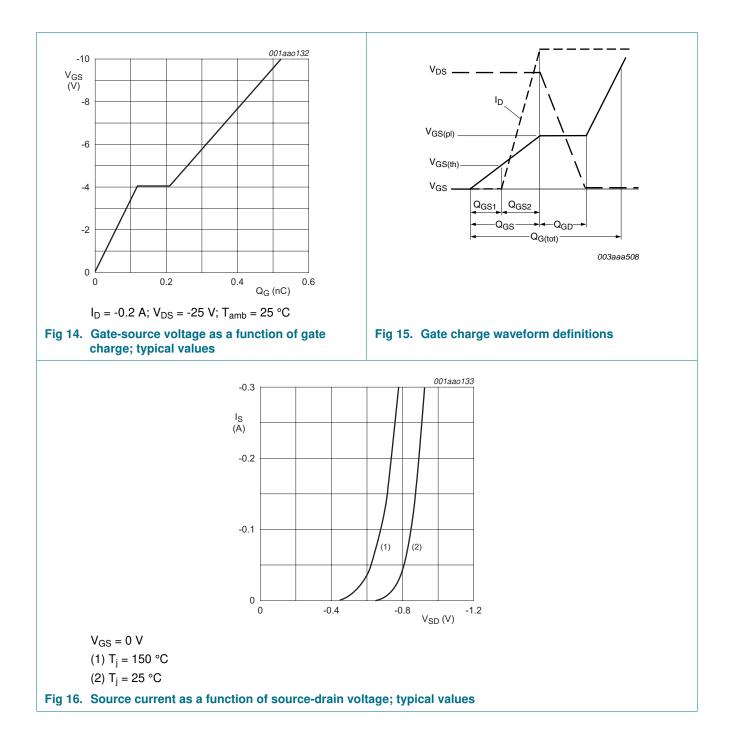
# **BSS84AK**

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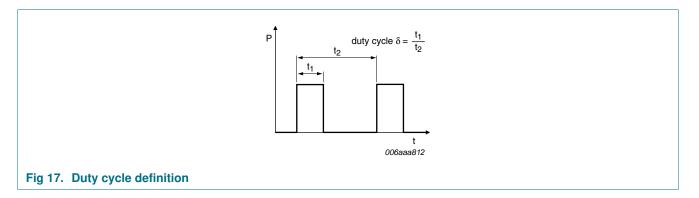


# BSS84AK

#### 50 V, 180 mA P-channel Trench MOSFET



### 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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### 9. Package outline

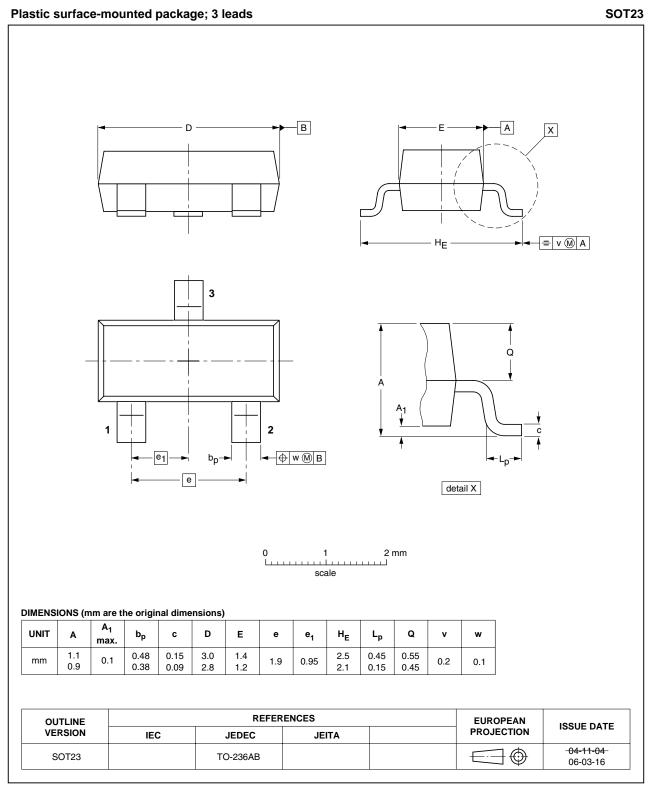
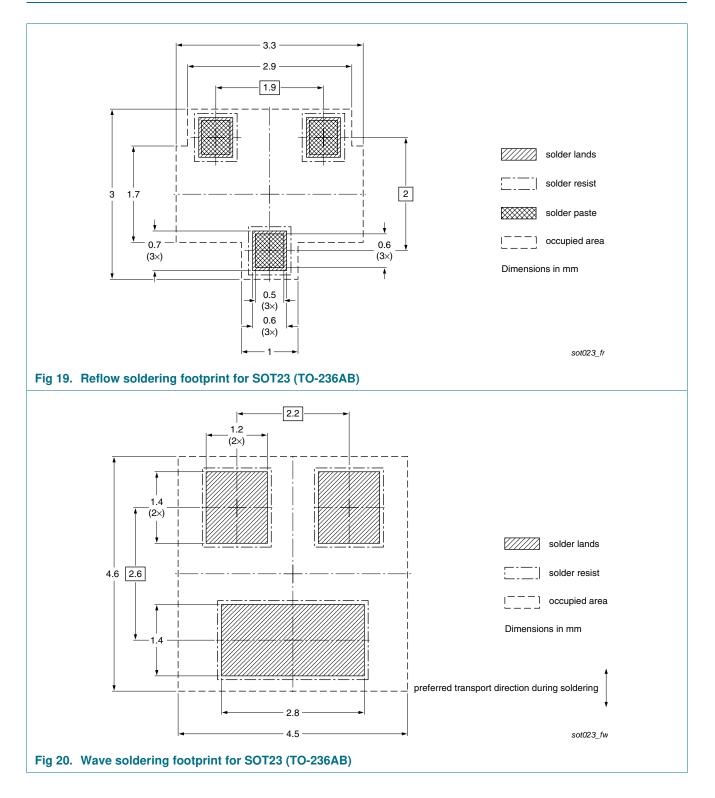


Fig 18. Package outline SOT23 (TO-236AB)

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#### 50 V, 180 mA P-channel Trench MOSFET

### 10. Soldering



# **11. Revision history**

Table 8.	Revision history						
Document	ID	Release date	Data sheet status	Change notice	Supersedes		
BSS84AK v	v.1	20110523	Product data sheet	-	-		

### 12. Legal information

#### 12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

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